

GUJARAT TECHNOLOGICAL UNIVERSITY

BE - SEMESTER-V EXAMINATION – SUMMER 2025

Subject Code:3151105

Date:20-05-2025

Subject Name:VLSI Design

Time:02:30 PM TO 05:00 PM

Total Marks:70

Instructions:

1. Attempt all questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.
4. Simple and non-programmable scientific calculators are allowed.

MARKS

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|------------|-----|--|-----------|
| Q.1 | (a) | Present device isolation techniques in fabrication process. | 03 |
| | (b) | Explain the MOS system under external bias. | 04 |
| | (c) | Describe the working of edge-triggered flip-flops with necessary diagrams. | 07 |
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| Q.2 | (a) | Explain the basic principles of pass transistor circuits. | 03 |
| | (b) | Design 2-input OR, AND and XOR gate using CMOS. | 04 |
| | (c) | Present the analysis of the resistive load inverter. Derive critical voltages and noise margins. | 07 |
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| OR | | | |
| | (c) | Analyze transmission gates (TGs) in detail. Also, describe the procedure for circuit design with TGs. | 07 |
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| Q.3 | (a) | Enlist MOSFET scaling and small-geometry effects. | 03 |
| | (b) | Discuss synchronous dynamic circuit techniques. | 04 |
| | (c) | Present timing analysis of CMOS inverter. | 07 |
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| OR | | | |
| Q.3 | (a) | What is the built-in self-test (BIST)? Explain this technique in brief. | 03 |
| | (b) | Describe the behavior of bistable elements. | 04 |
| | (c) | Explain voltage bootstrapping. | 07 |
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| Q.4 | (a) | Write the equations describing the current-voltage characteristics of MOSFET. | 03 |
| | (b) | Describe fabrication of nMOS Transistor. | 04 |
| | (c) | Analyze the factors behind latch-up problems. Also, explain the techniques for its prevention. | 07 |
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| OR | | | |
| Q.4 | (a) | What is the substrate bias effect? Explain its analysis. | 03 |
| | (b) | Discuss switching power dissipation of CMOS inverters. | 04 |
| | (c) | Present the analysis of on-chip clock generation and distribution techniques. | 07 |
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| Q.5 | (a) | Define and explain DIBL. | 03 |
| | (b) | Present delay-time definitions. | 04 |
| | (c) | Discuss fault types and models. | 07 |
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| OR | | | |
| Q.5 | (a) | Explain controllability and observability. | 03 |
| | (b) | Describe the operating principle of the SR latch circuit with the necessary diagrams. | 04 |
| | (c) | What are the needs of FinFET devices? Explain FinFET devices in detail. Also, compare them with planar MOSFET. | 07 |
